

# 2N7002W, 2V7002W

## Small Signal MOSFET

60 V, 340 mA, Single, N-Channel, SC-70

### Features

- ESD Protected
- Low  $R_{DS(on)}$
- Small Footprint Surface Mount Package
- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter
- Portable Applications i.e. DSC, PDA, Cell Phone, etc.

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	60	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current (Note 1) Steady State	$I_D$	$T_A = 25^\circ\text{C}$ 310	mA
		$T_A = 85^\circ\text{C}$ 220	
$t < 5$ s	$I_D$	$T_A = 25^\circ\text{C}$ 340	mA
		$T_A = 85^\circ\text{C}$ 240	
Power Dissipation (Note 1) Steady State $t < 5$ s	$P_D$	280 330	mW
Pulsed Drain Current ( $t_p = 10$ $\mu$ s)	$I_{DM}$	1.4	A
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	$-55$ to $+150$	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	250	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	450	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5$ s (Note 1)	$R_{\theta JA}$	375	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

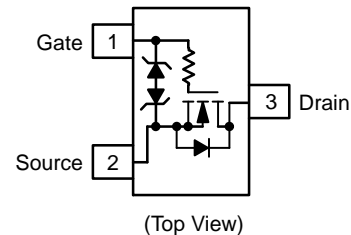


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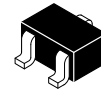
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX (Note 1)
60 V	1.6 $\Omega$ @ 10 V	340 mA
	2.5 $\Omega$ @ 4.5 V	

### SIMPLIFIED SCHEMATIC

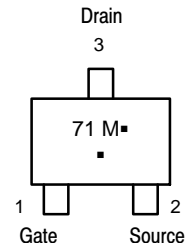


(Top View)

### MARKING DIAGRAM & PIN ASSIGNMENT



SC-70/SOT-323  
CASE 419  
STYLE 8



71 = Device Code  
M = Date Code  
■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
2N7002WT1G	SC-70 (Pb-Free)	3000/Tape & Reel
2V7002WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# 2N7002W, 2V7002W

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			71		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 60 V	T <sub>J</sub> = 25°C		1.0	μA
			T <sub>J</sub> = 150°C		15	μA
		V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V	T <sub>J</sub> = 25°C		100	nA
			T <sub>J</sub> = 150°C		10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±10	μA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±10 V			450	nA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±5.0 V			150	nA

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1.0		2.5	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			4.0		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 500 mA		1.19	1.6	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 200 mA		1.33	2.5	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 200 mA		530		mS

### CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 20 V		24.5		pF
Output Capacitance	C <sub>OSS</sub>			4.2		
Reverse Transfer Capacitance	C <sub>RSS</sub>			2.2		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V; I <sub>D</sub> = 200 mA		0.7		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			0.1		
Gate-to-Source Charge	Q <sub>GS</sub>			0.3		
Gate-to-Drain Charge	Q <sub>GD</sub>			0.1		

### SWITCHING CHARACTERISTICS, V<sub>GS</sub> = V (Note 3)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DD</sub> = 25 V, I <sub>D</sub> = 500 mA, R <sub>G</sub> = 25 Ω		12.2		ns
Rise Time	t <sub>r</sub>			9.0		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			55.8		
Fall Time	t <sub>f</sub>			29		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 200 mA	T <sub>J</sub> = 25°C		0.8	1.2	V
			T <sub>J</sub> = 85°C		0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

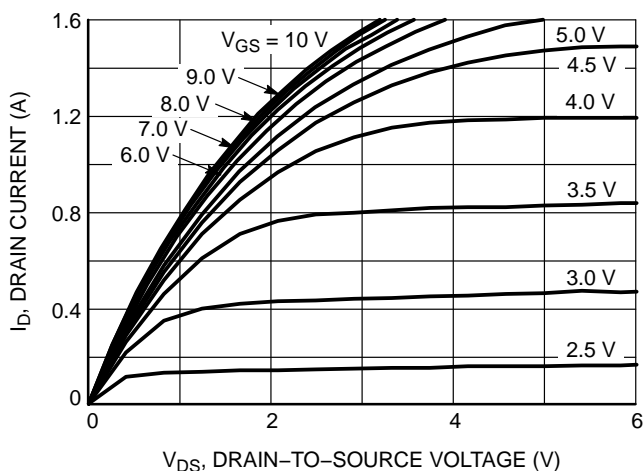


Figure 1. On-Region Characteristics

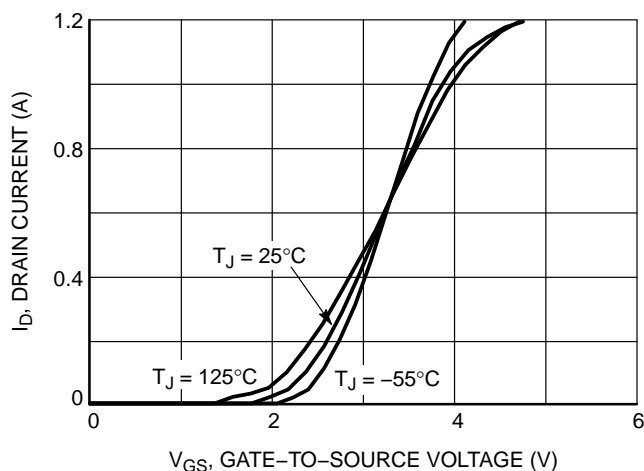


Figure 2. Transfer Characteristics

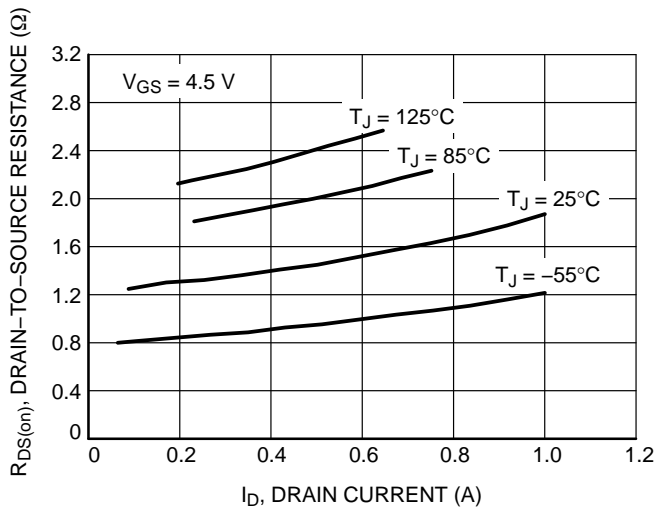


Figure 3. On-Resistance vs. Drain Current and Temperature

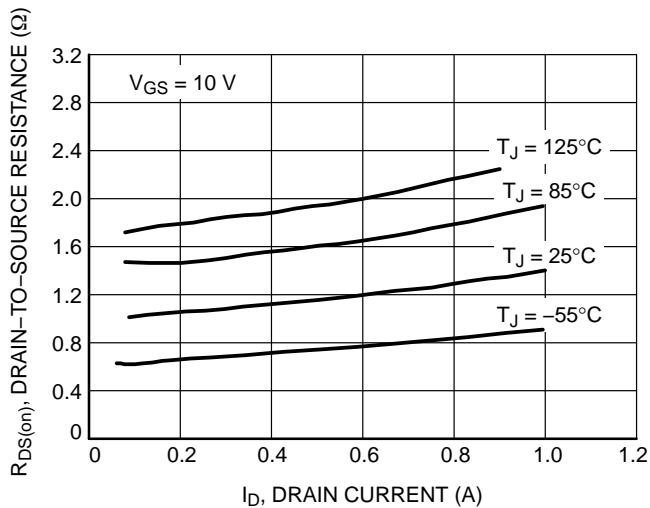


Figure 4. On-Resistance vs. Drain Current and Temperature

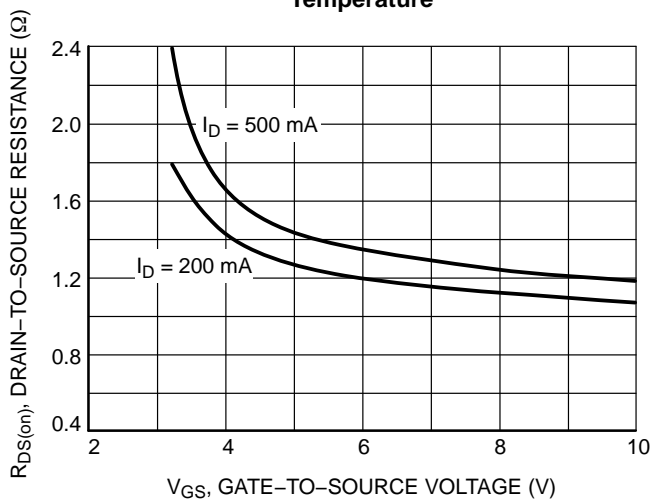


Figure 5. On-Resistance vs. Gate-to-Source Voltage

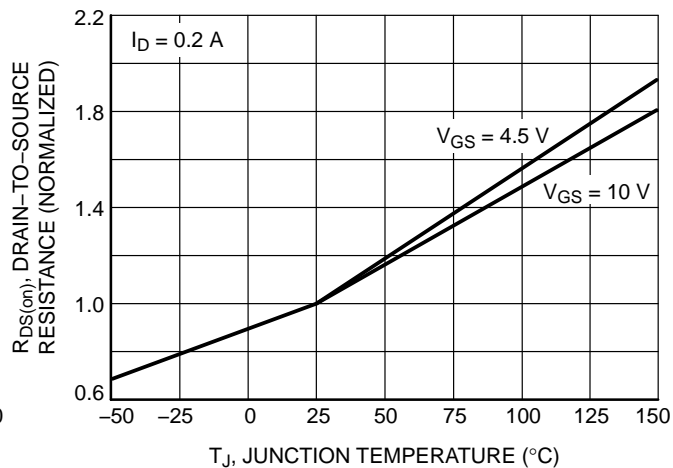


Figure 6. On-Resistance Variation with Temperature

TYPICAL CHARACTERISTICS

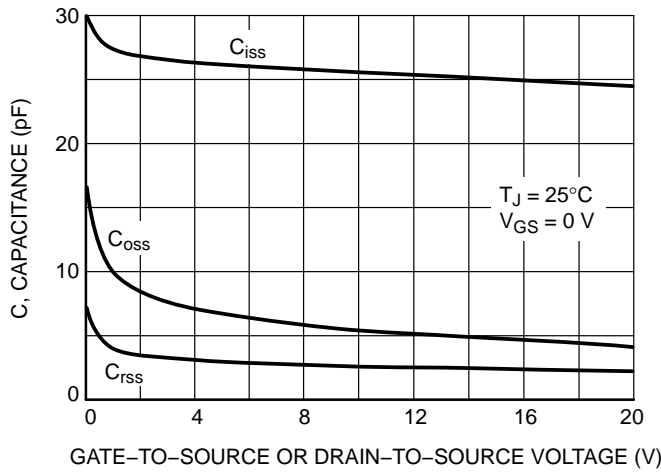


Figure 7. Capacitance Variation

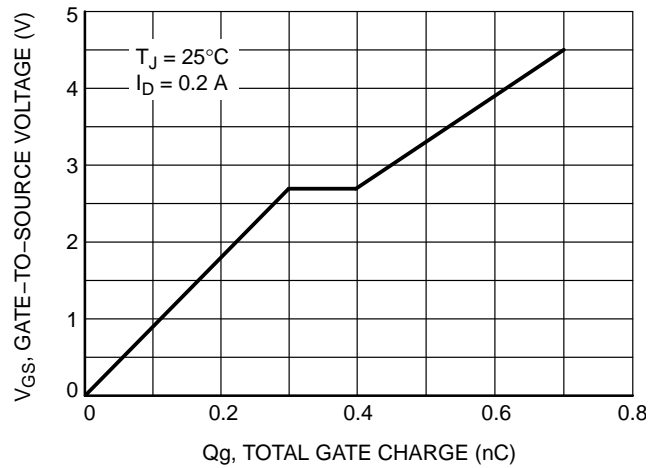


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

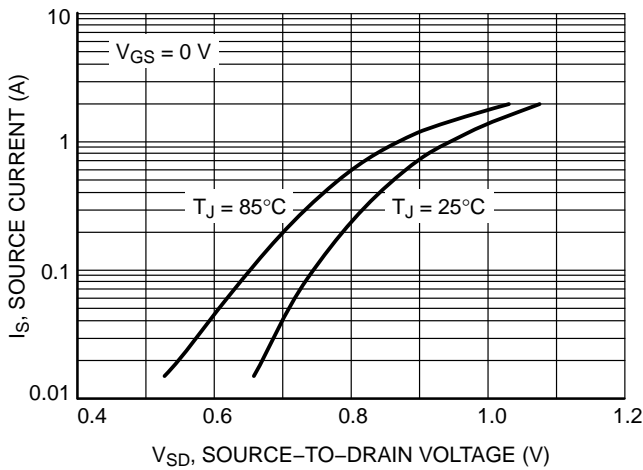


Figure 9. Diode Forward Voltage vs. Current

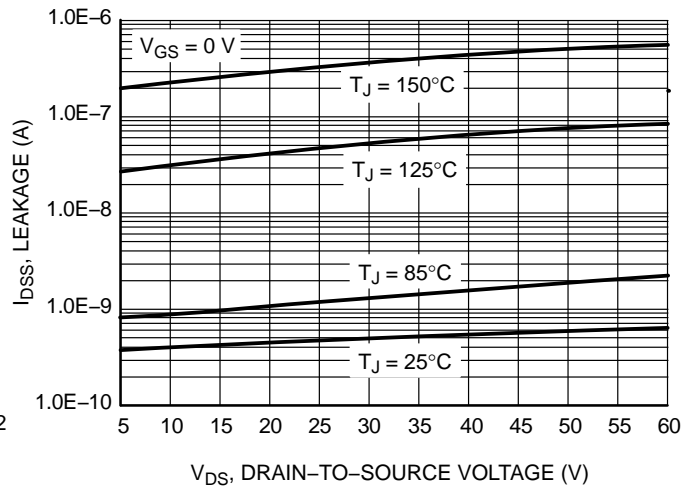
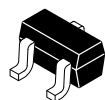


Figure 10. Drain-to-Source Leakage Current vs. Voltage



SCALE 4:1

### SC-70 (SOT-323)

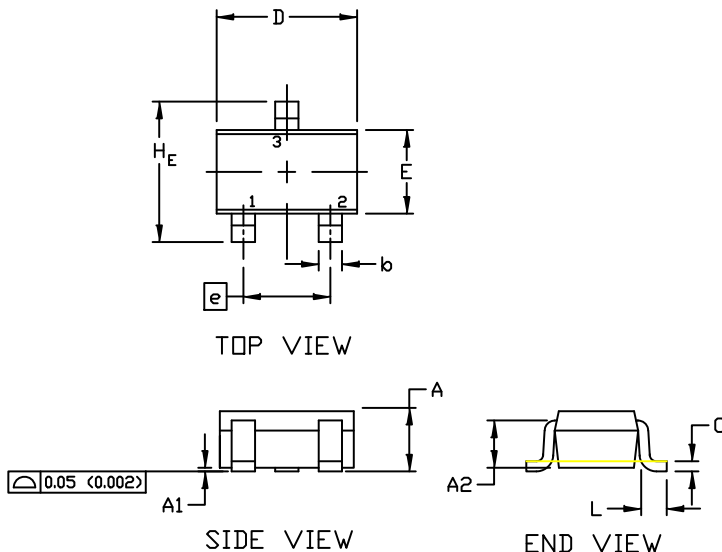
#### CASE 419

#### ISSUE P

DATE 07 OCT 2021

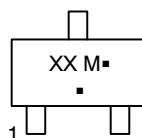
#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH



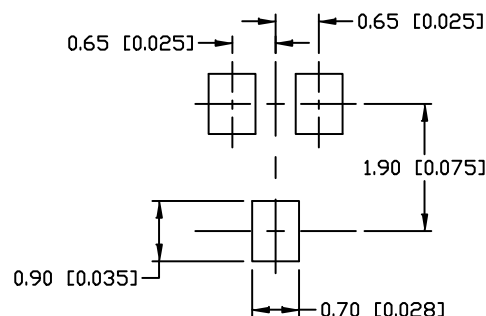
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

#### GENERIC MARKING DIAGRAM



XX = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### SOLDERING FOOTPRINT

STYLE 1:  
CANCELLED

STYLE 2:  
PIN 1. ANODE  
2. N.C.  
3. CATHODE

STYLE 3:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 6:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 7:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 8:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 9:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 10:  
PIN 1. CATHODE  
2. ANODE  
3. ANODE-CATHODE

STYLE 11:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

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